

MSF6N70

700V N-Channel MOSFET

Description

The MSF6N70 is a N-channel enhancement-mode MOSFET , providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220F package is universally preferred for all commercial-industrial applications

Features

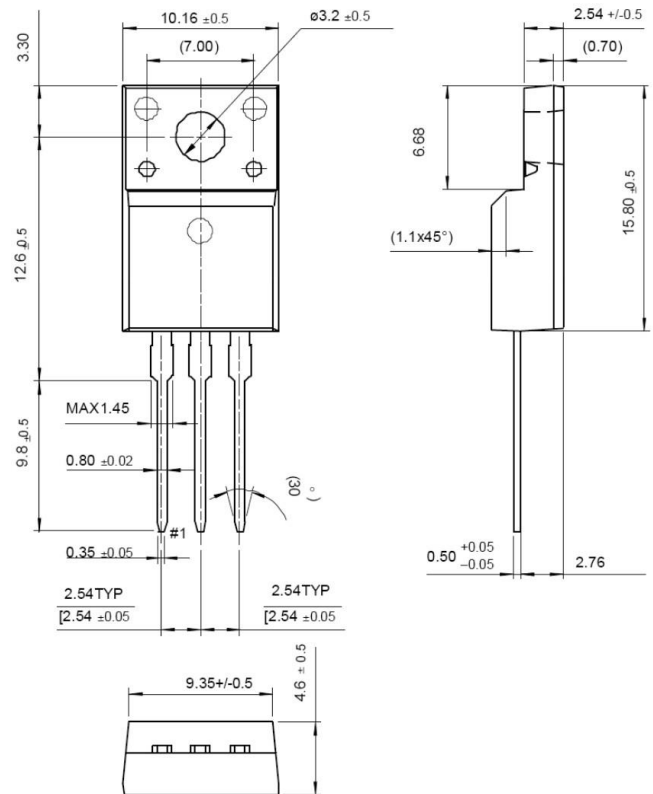
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant / Halogen free package available

Application

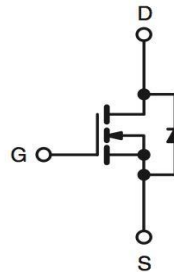
- Adapter
- Switching Mode Power Supply

Packing & Order Information

50/Tube ; 1,000/Box



Graphic symbol



**RoHS
COMPLIANT**

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	700	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current -Continuous (TC=25°C)	6.0	A
	Drain Current -Continuous (TC=100°C)	3.5	A
I _{DM}	Drain Current Pulsed	22	A
E _{AS}	Single Pulsed Avalanche Energy	350	mJ
E _{AR}	Repetitive Avalanche Energy	14.7	mJ
dv/dt	Peak Diode Recovery dv/dt	5.5	V/ns
P _D	Power Dissipation (TC=25°C)	48	W
	Power Dissipation (TC=100°C)	0.38	W/°C

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Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS}=5.5A, V_{DD}=50V, L=8mH, V_G=10V, starting T_J=+25°C.
3. I_{SD}≤5.5A, dI/dt≤100A/μs, V_{DD}≤BVDSS, starting T_J=+25°C.
4. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature

Static Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
V _{GS}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
*R _{DS(ON)}	V _{GS} = 10 V , I _D = 2.8 A	--	1.5	1.8	Ω
BV _{DSS}	V _{GS} = 0 V , I _D = 250μA	700	--	--	V
ΔBV _{DSS} /ΔT _J	I _D = 250μA, Referenced to 25°C		0.7		
I _{DSS}	V _{DS} = 700 V , V _{GS} = 0 V V _{DS} = 560 V , V _{GS} = 0 V , T _J = 125°C	--	--	1 10	uA
I _{GSSF}	V _{DS} = 30 V, V _{GS} = 0 V			100	nA
I _{GSSR}	V _{DS} = -30 V, V _{GS} = 0 V	--	--	-100	nA

Dynamic Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0MHz	--	1100	1500	pF
C _{OSS}		--	110	150	pF
C _{RSS}		--	12	16	pF
t _{d(on)}	V _{DS} = 350 V, I _D = 5.5 A, R _G = 25 Ω	--	10	30	ns
t _r		--	35	80	ns
t _{d(off)}		--	45	100	ns
t _f		--	40	90	ns
Q _g	V _{DS} = 560 V, I _D = 5.5 A, V _{GS} = 10 V	--	29	37	nC
Q _{gs}		--	5	--	
Q _{gd}		--	11	--	

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Source-Drain Diode Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
I_S		--	--	5.5	A
I_{SM}		--	--	22	
V_{SD}	$I_F = 5.5 \text{ A}$, $V_{GS} = 0$	--	--	1.5	V
t_{rr}	$I_F = 5.5 \text{ A}$, $V_{GS} = 0$, $dI_F/dt = 100\text{A}/\mu\text{s}$	--	390	--	ns
Q_{rr}		--	3.6	--	uC

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■ Characteristics Curve

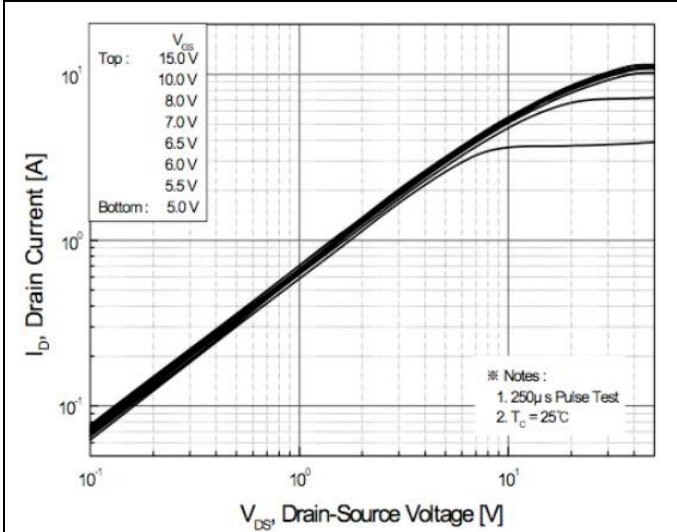


FIG.1-ON REGION CHARACTERISTICS

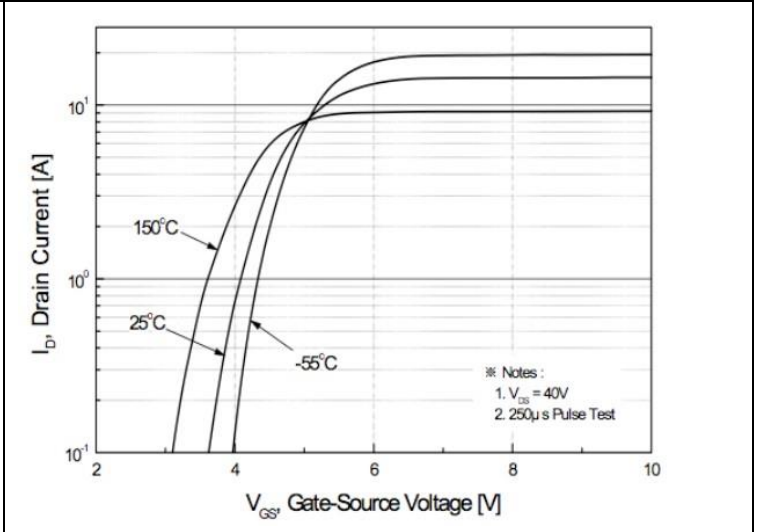


FIG.2-TRANSFER CHARACTERISTICS

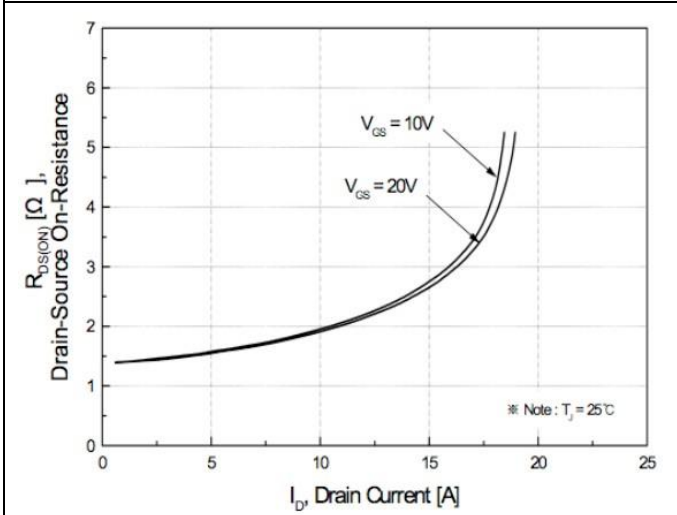


FIG.3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

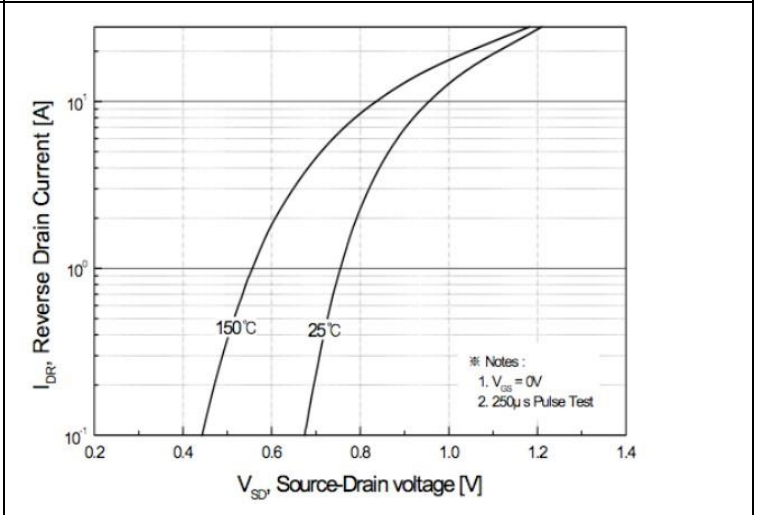


FIG.4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

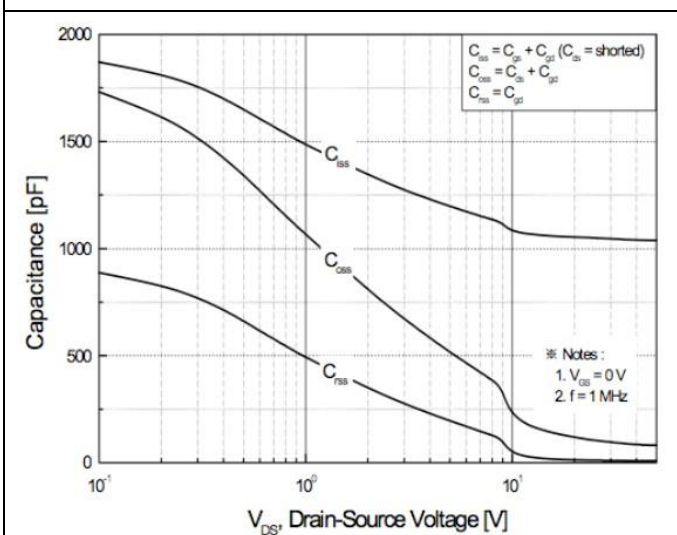


FIG.5-CAPACITANCE CHARACTERISTICS

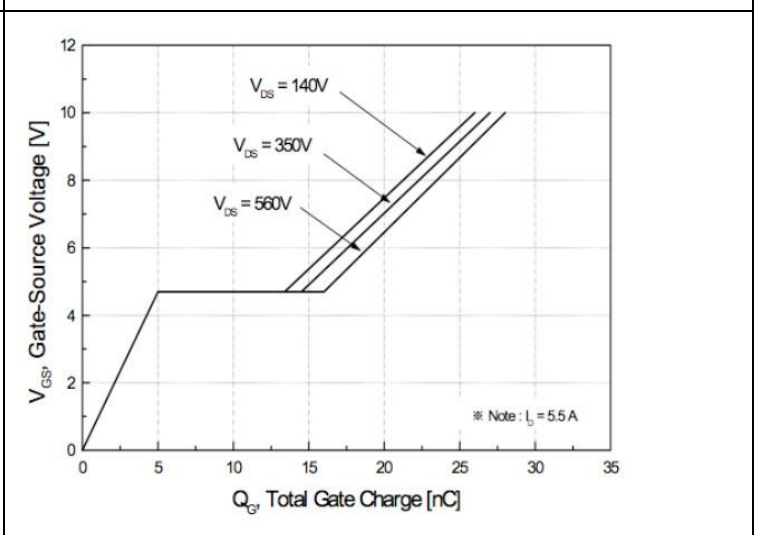


FIG.6-GATE CHARGE CHARACTERISTICS

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Characteristics Curve

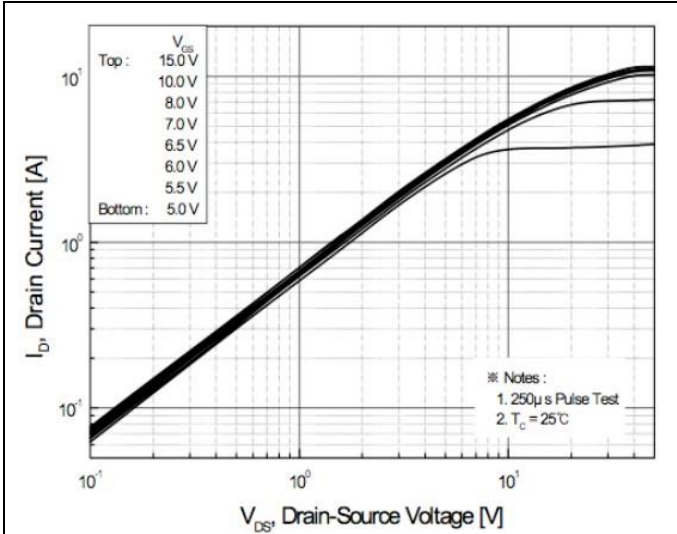


FIG.1-ON REGION CHARACTERISTICS

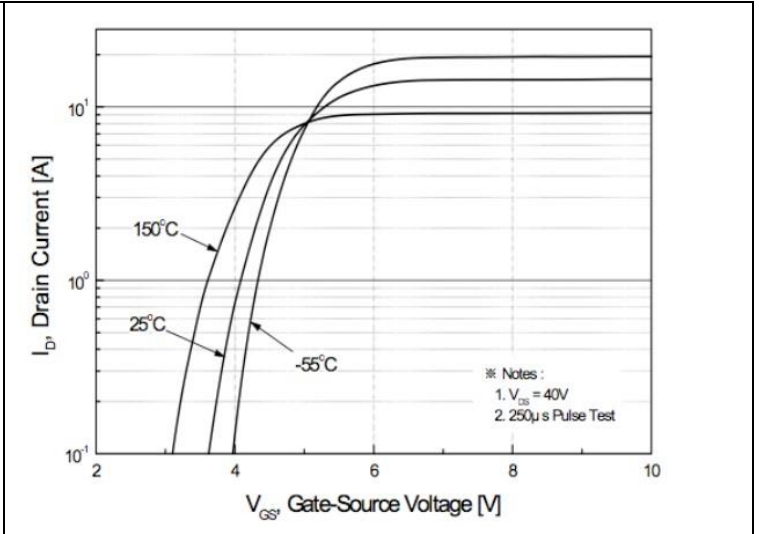


FIG.2-TRANSFER CHARACTERISTICS

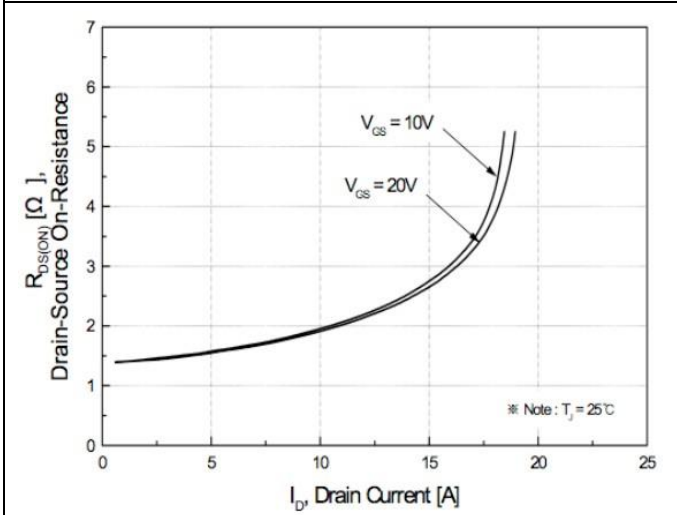


FIG.3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

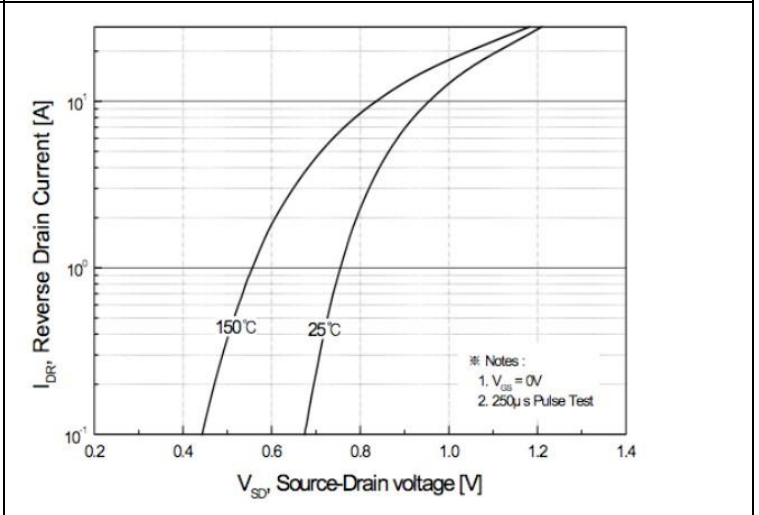


FIG.4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

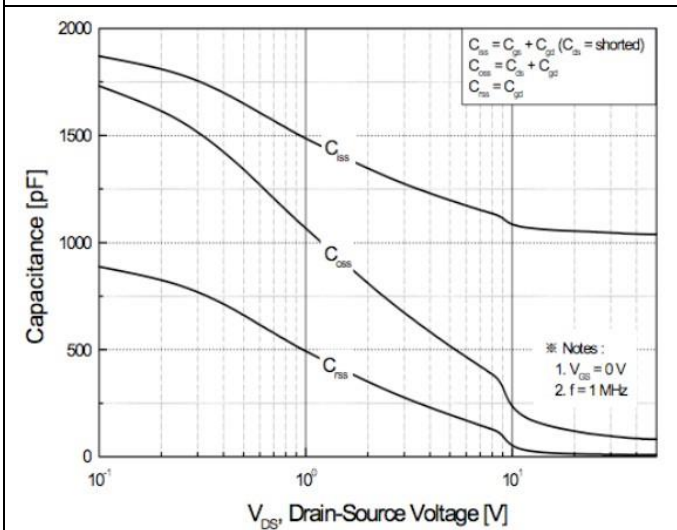


FIG.5-CAPACITANCE CHARACTERISTICS

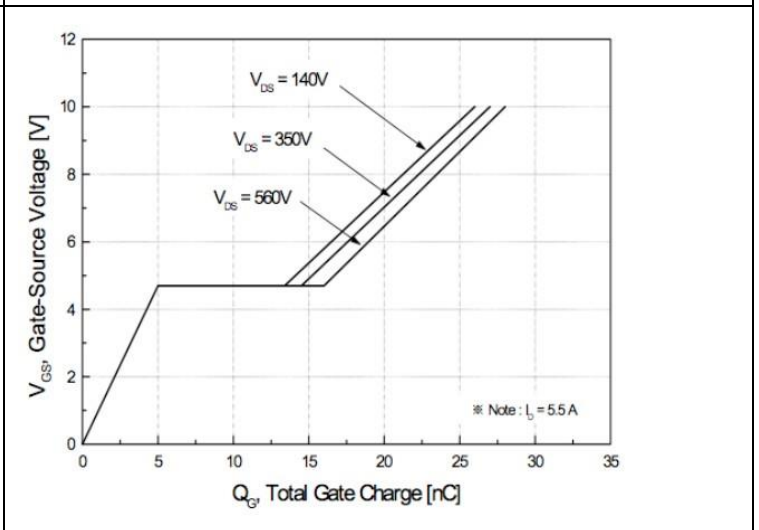
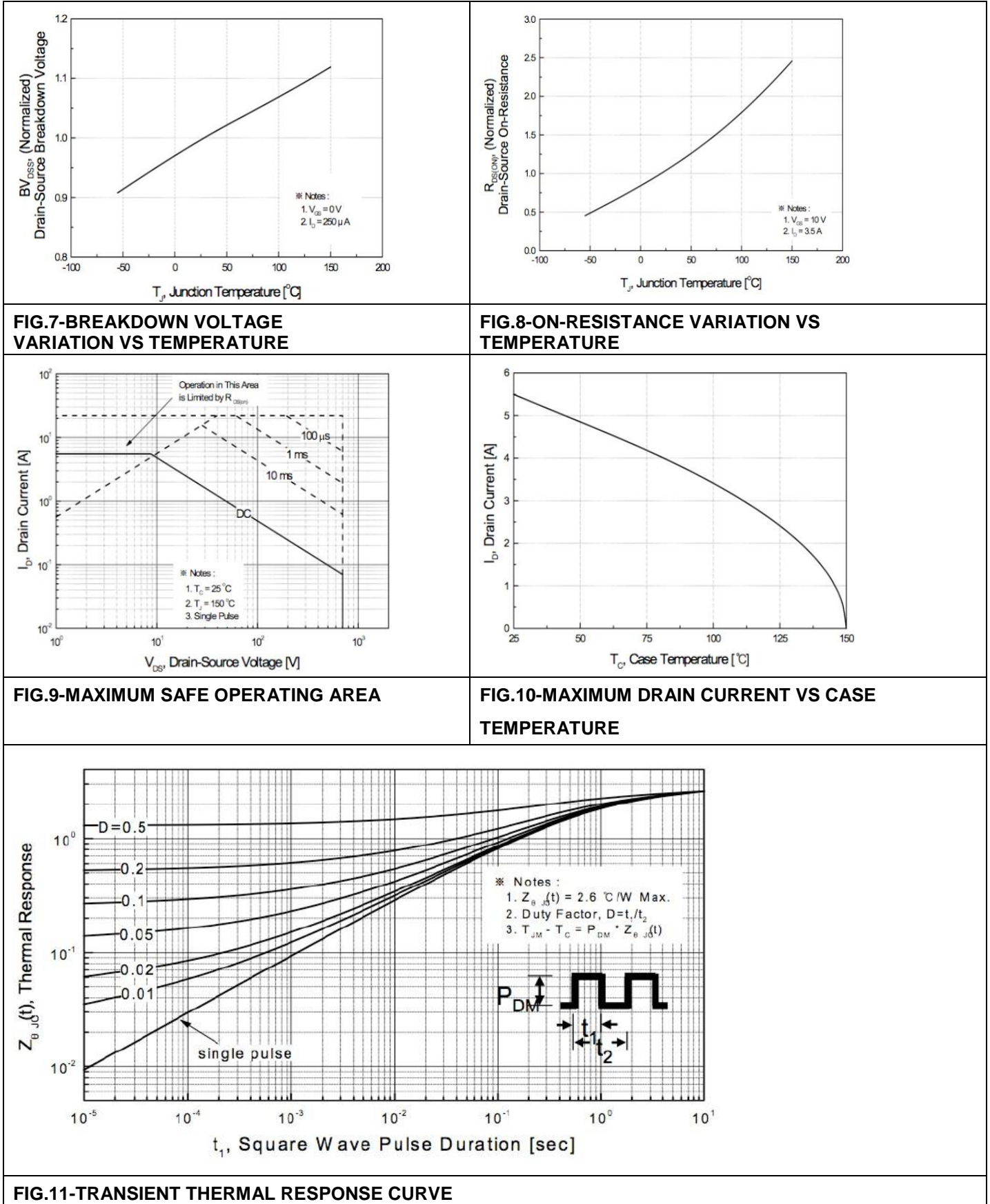


FIG.6-GATE CHARGE CHARACTERISTICS

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Characteristics Test Circuit & Waveform



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■ Characteristics Test Circuit & Waveform

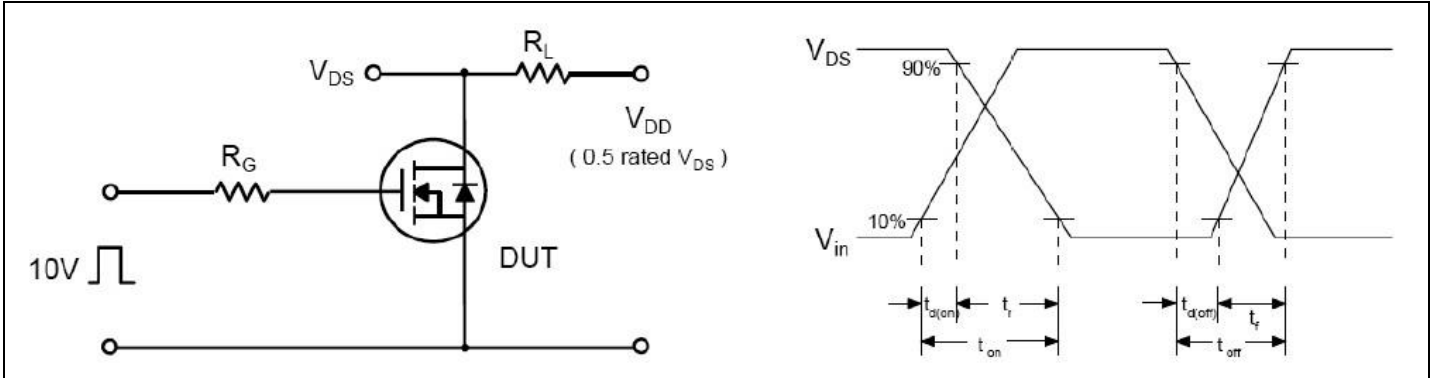


Fig 12. Resistive Switching Test Circuit & Waveforms

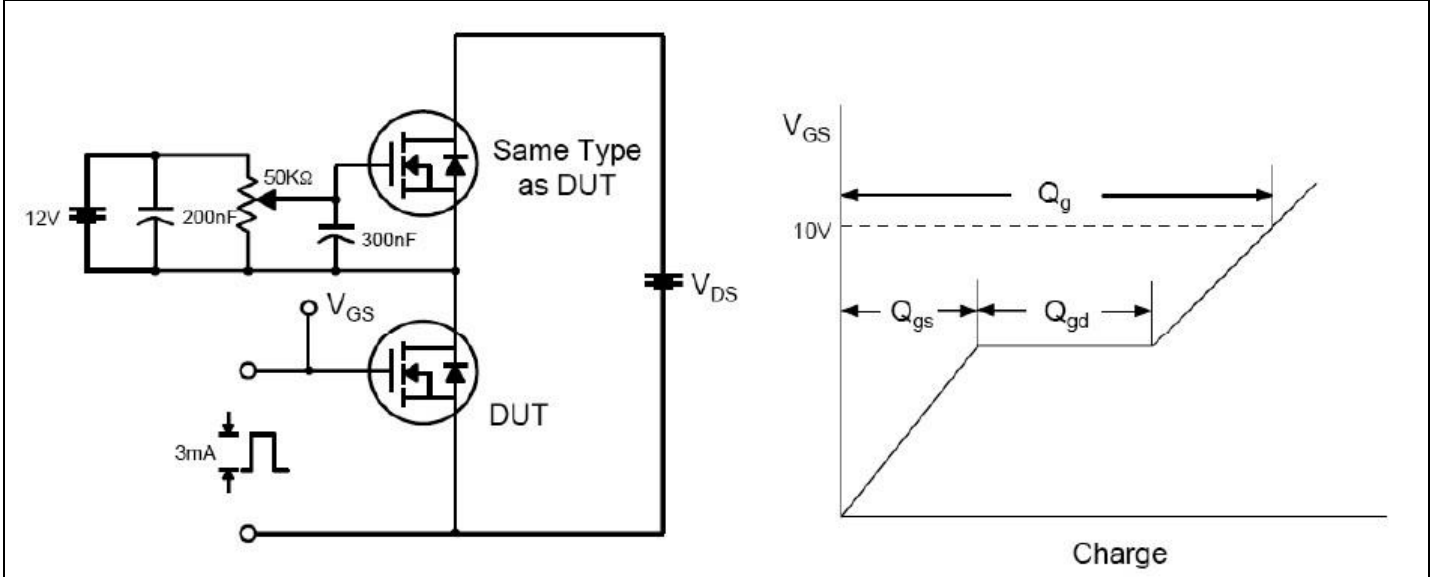


Fig 13. Gate Charge Test Circuit & Waveform

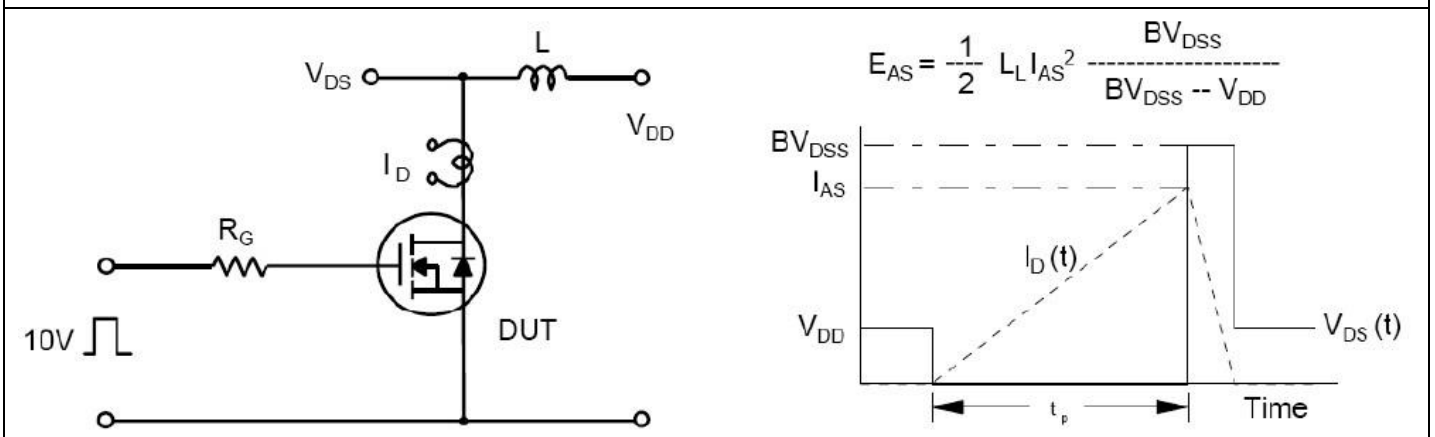


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

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